Electronic Supplementary Material (ESI) for Journal of Materials Chemistry C.

Supporting Information

Improving Device Performance of n-type Organic Field-Effect Transistors via Doping with p-type Organic Semiconductor

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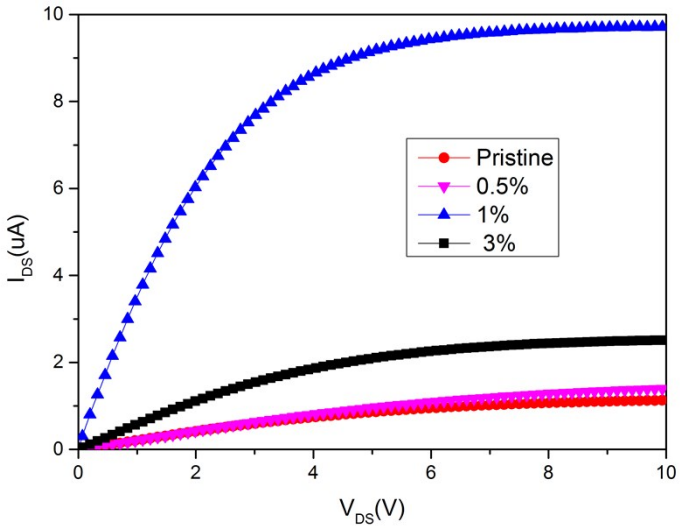
a)



b)

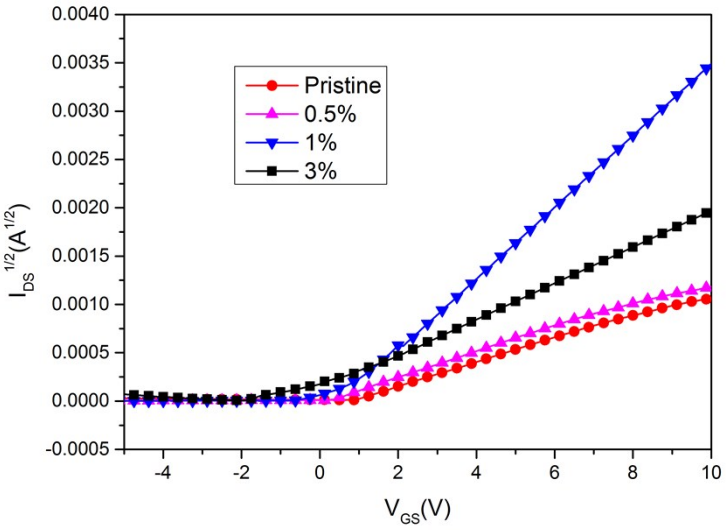


Figure S1 a) Output curve, b) $I_d^{1/2}$ vs V_{GS} plot of the pristine and blend OFETs.

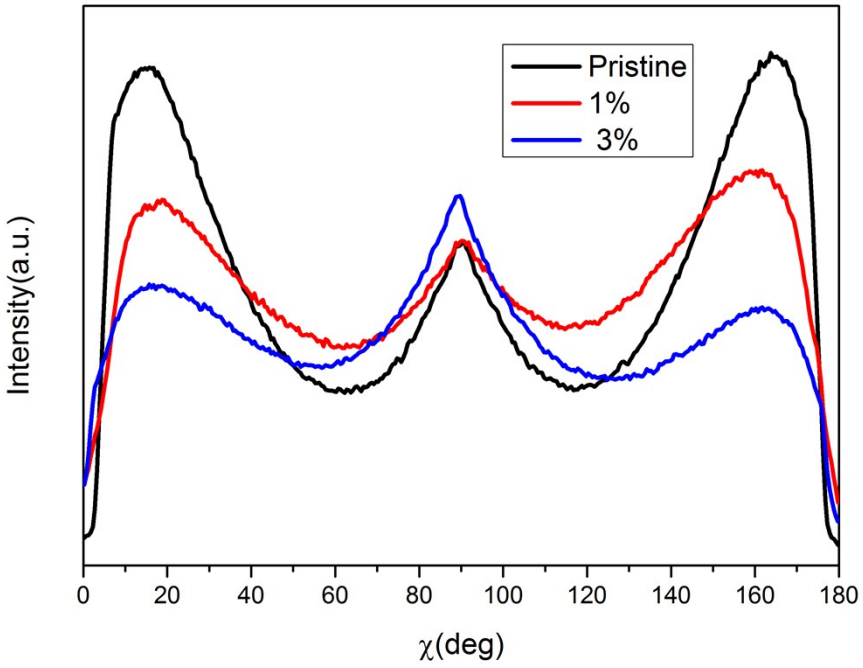


Figure S2 Pole figures extracted from the (100) lamellar diffraction for the pristine film and blend films.

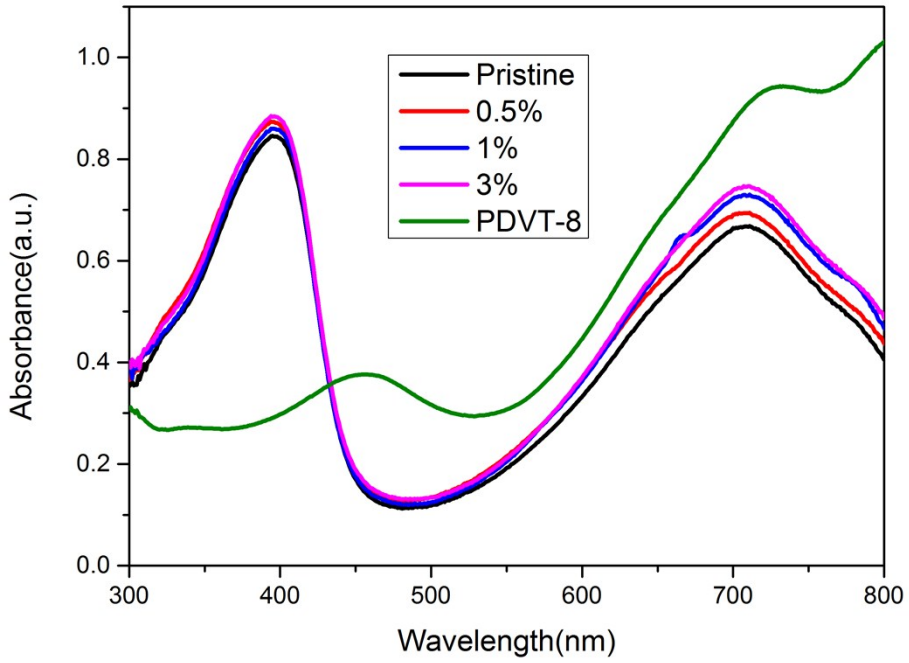


Figure S3 Normalized UV-vis absorption spectra of pristine N2200 film, PDVT-8 films and PDVT-8 blended N2200.

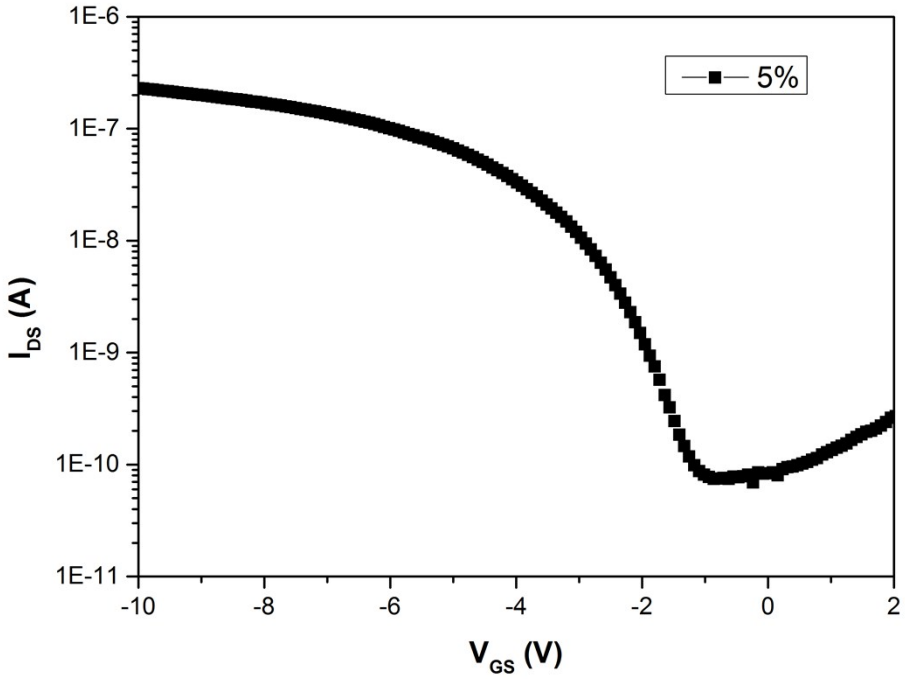


Figure S4 P-type transfer characteristic of the device based on N2200 containing 5% PVDT-8.

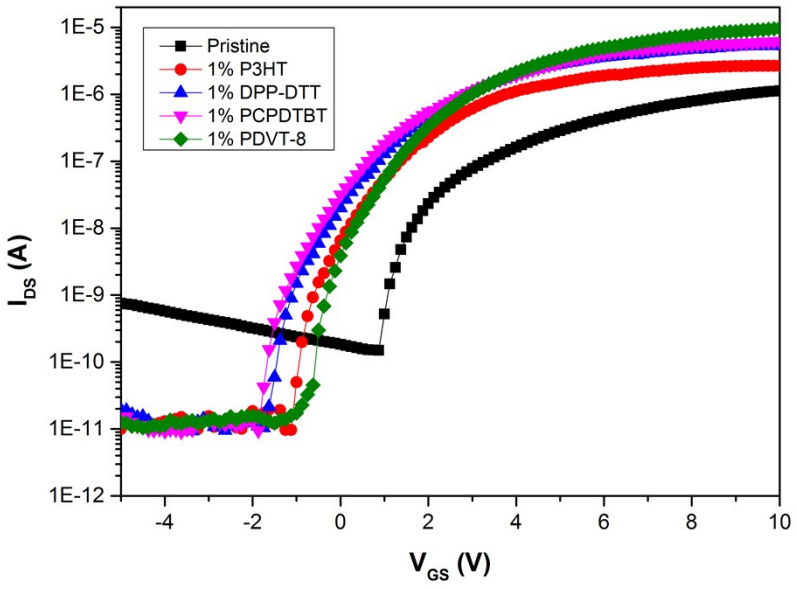


Figure S5 Transfer characteristics of pristine N2200 and its blends with P3HT, DPP-DTT, PCPDTBT and PDVT-8.

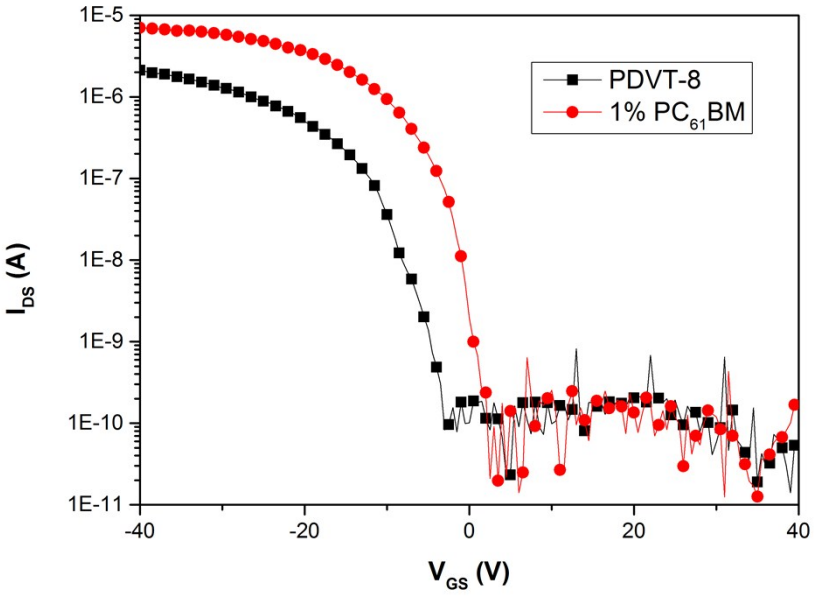


Figure S6 Transfer characteristics of pristine P-type polymer PDVT-8 and its blends with 1% PCBM.